

In re the Application of:

KANDA

Serial No. 09/607,219

Filed: June 30, 2000

For: SEMICONDUCTOR DEVICES AND  
METHODS OF FABRICATING  
THE SAME

Group Art Unit: 2814

Examiner: Quach, T.

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ASSISTANT COMMISSIONER OF PATENTS  
Washington, D.C. 20231

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Sir:

Transmitted herewith is an Amendment in the above-identified application.

Small entity status of this application under 37 CFR 1.9 and 1.27 has been established by a verified statement previously submitted.

A verified statement to establish small entity status under 37 CFR 1.9 and 1.27 is enclosed.

No additional fee is required.

The fee has been calculated as shown below:

	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NO PREVIOUSLY PAID FOR		PRESENT EXTRA RATE		ADDIT. FEE	OR	RATE		ADDIT. FEE
TOTAL	25	MINUS	47	=	0	x	\$0	OR	x 18	\$0	
INDEP CLAIMS *	3	MINUS	5	=	0	x	\$0	OR	x 84	\$0	
						+	\$	OR	+ 280	\$0	
FIRST PRESENTATION OF MULTIPLE DEP. CLAIM											
					TOTAL		\$0	OR	TOTAL	\$0	

Please charge Deposit Account No. 50-0585 the amount of \$\_\_\_\_\_ to cover the extension fee and also the amount of \$\_\_\_\_\_ to cover the claim fee. A duplicate copy of this sheet is enclosed.

- ☒ A check in the amount of \$ 920 to cover the extension fee is enclosed.  
☐ A check in the amount of \$ \_\_\_\_\_ to cover the filing fee for additional claims is enclosed.  
☐ A check in the amount of \$ \_\_\_\_\_ to cover the petition fee is enclosed.  
☐ A check in the amount of \$ \_\_\_\_\_ to cover the Information Disclosure Statement fee is enclosed.

☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 50-0585. A duplicate of this sheet is enclosed.

☒ Any filing fees under 37 CFR 1.16 for the presentation of extra claims.

☒ Any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

*Alan S. Raynes*

Dated: April , 2002

Alan S. Raynes

Registration No. 39,809

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on April 24, 2002.

*Alan S. Raynes*  
Alan S. Raynes

*April 24, 2002*  
Date

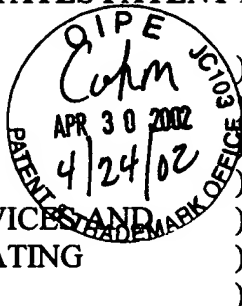
## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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AMENDMENTAssistant Commissioner for Patents  
Washington, DC 20231

Dear Sirs:

In response to the Office Action dated October 24, 2001, the response being due by April 24, 2002 by the enclosed Petition for Extension of Time, please enter and consider the following.

IN THE CLAIMS:

Please cancel claims 1-47 without prejudice.

Please add new claims 48-72 as follows:

--48. (new) A method of fabricating a semiconductor device comprising:

forming a pad;

forming a protective insulating region on the pad by forming first and second insulating layers, the first insulating layer being in direct contact with the pad and the second insulating layer being in direct contact with the first insulation layer;

forming a mask layer on the protective insulating region in direct contact with a surface of the second insulation layer, the second insulation layer being positioned between the first insulating layer and the mask layer, the mask layer including an aperture in a region corresponding to an electric connection region of the pad; and

dry etching through the surface of the second insulation layer at the aperture in the mask to form an opening extending through the second insulating layer and the first insulating layer to the pad.